

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	15748	(plasma adj enhanced adj chemical adj vapor adj deposition) or PECVD	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:03
2	BRS	L2	21430	tetraethylorthosilicate or TEOS	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:03
3	BRS	L4	141731 7	trench or gap or plug	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:04
4	BRS	L5	132762 6	oxide or SiO	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:05
5	BRS	L6	388012 4	remov\$6 or etch\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:06

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L7	73374	MOSFET or "metal oxide semiconductor field effect"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:06
7	BRS	L9	9931	6 near8 5 near8 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:09
8	BRS	L10	1060	9 and 1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:11
9	BRS	L11	548	10 and 2	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:11
10	BRS	L12	108	11 and 7	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:49

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L13	35535	wetch-etching or wetch-etched or wet-etch or (wet adj etch\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:50
12	BRS	L14	2975	9 and 13	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:51
13	BRS	L15	988	9 same 13	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:51
14	BRS	L16	197	15 and 7	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:51
15	IS&R	L43	1671	(438/270).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 18:21

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	15748	(plasma adj enhanced adj chemical adj vapor adj deposition) or PECVD	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:03
2	BRS	L2	21430	tetraethylorthosilicate or TEOS	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:03
3	BRS	L4	141731 7	trench or gap or plug	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:04
4	BRS	L5	132762 6	oxide or SiO	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:05
5	BRS	L6	388012 4	remov\$6 or etch\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:06

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L7	73374	MOSFET or "metal oxide semiconductor field effect"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:06
7	BRS	L9	9931	6 near8 5 near8 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:09
8	BRS	L10	1060	9 and 1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:11
9	BRS	L11	548	10 and 2	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:11
10	BRS	L12	108	11 and 7	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:49

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L13	35535	wetch-etching or wetch-etched or wet-etch or (wet adj etch\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:50
12	BRS	L14	2975	9 and 13	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:51
13	BRS	L15	988	9 same 13	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:51
14	BRS	L16	197	15 and 7	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 16:51
15	IS&R	L43	1671	(438/270).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 18:21

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	IS&R	L44	89	(438/269).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 18:22
17	IS&R	L45	1208	(438/424).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 18:22
18	IS&R	L46	687	(438/633).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 18:22
19	IS&R	L47	956	(438/689).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 18:22
20	IS&R	L48	605	(438/691).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 18:22

	Type	L #	Hits	Search Text	DBs	Time Stamp
21	IS&R	L49	1807	(438/692) .CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/05 18:22

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	IS&R	L1	965	(438/689).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/06 14:04
2	IS&R	L2	689	(438/633).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/06 14:26
3	BRS	L3	35616	wetch-etching or wetch-etched or wet-etch or (wet adj etch\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/06 14:27
4	BRS	L4	158	3 near4 oxide near4 trench\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/06 14:27
5	IS&R	L5	605	(438/691).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/06 14:45

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	IS&R	L6	1809	(438/692) .CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/06 15:36
7	IS&R	L7	1672	(438/270) .CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/06 15:42

	Type	Hits	Search Text
1	BRS	15748	(plasma adj enhanced adj chemical adj vapor adj deposition) or PECVD
2	BRS	21430	tetraethylorthosilicate or TEOS
3	BRS	1417317	trench or gap or plug
4	BRS	1327626	oxide or SiO
5	BRS	3880124	remov\$6 or etch\$6
6	BRS	73374	MOSFET or "metal oxide semiconductor field effect"
7	BRS	9931	(remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)
8	BRS	1060	((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) and ((plasma adj enhanced adj chemical adj vapor adj deposition) or PECVD)
9	BRS	548	((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) and ((plasma adj enhanced adj chemical adj vapor adj deposition) or PECVD)) and (tetraethylorthosilicate or TEOS)
10	BRS	108	((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) and ((plasma adj enhanced adj chemical adj vapor adj deposition) or PECVD)) and (tetraethylorthosilicate or TEOS)) and (MOSFET or "metal oxide semiconductor field effect")
11	BRS	2975	((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) and (wetch-etching or wetch-etched or wet-etch or (wet adj etch\$6))
12	BRS	988	((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) same (wetch-etching or wetch-etched or wet-etch or (wet adj etch\$6))

	DBs	Time Stamp
1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/05 16:03
2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/05 16:03
3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/05 16:04
4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/05 16:05
5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/05 16:06
6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/05 16:06
7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/05 16:09
8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/05 16:11
9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/05 16:11
10	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/05 16:49
11	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/05 16:51
12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/05 16:51

	Type	Hits	Search Text
13	BRS	197	((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) same (wetch-etching or wetch-etched or wet-etch or (wet adj etch\$6))) and (MOSFET or "metal oxide semiconductor field effect")
14	IS&R	2	("20020081817").PN.
15	IS&R	89	(438/269).CCLS.
16	IS&R	1212	(438/424).CCLS.

	DBs	Time Stamp
13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/05 16:51
14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/06 09:48
15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/06 10:14
16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/06 10:37